

Docket No.: M4065.0111/P111-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Howard E. Rhodes, et al

Application No.: 09/780,390

Group Art Unit: 2825

Filed: February 12, 2001

Examiner: L. Malsawma

For: OPTIMIZED LOW LEAKAGE DIODES,
INCLUDING PHOTODIODES

8/8 Amdt
5.8.03
Awalk

AMENDMENT

Box Non-Fee Amendment
Commissioner for Patents
Washington, DC 20231

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MAY 05 2003

TECHNOLOGY CENTER 2800

Dear Sir:

In response to the Office Action dated February 4, 2003 (Paper No. 7), please amend the above-identified U.S. patent application as follows:

In the claims:

Please rewrite claims 1, 16-23, 28, 50 and 67 as follows:

1. (Amended) A diode, said diode comprising:
- an isolation region formed in a substrate;
 - a first doped active layer of a first conductivity type formed in said substrate, wherein said doped active layer is spaced apart from said isolation region;
 - a second doped active layer of a second conductivity type in contact with said first doped active layer, the contact of said first and second active layers forming a p-n junction;
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